

2SD1846

Silicon NPN Triple-Diffused Planar Type

Horizontal Deflection Output

■ Features

- Damper diode built-in
- Minimizes external component counts and simplifies circuitry
- High breakdown voltage, high reliability
- High speed switching
- Wide area of safety operation (ASO)
- "Full Pack" package for simplified mounting on a heat sink with one screw

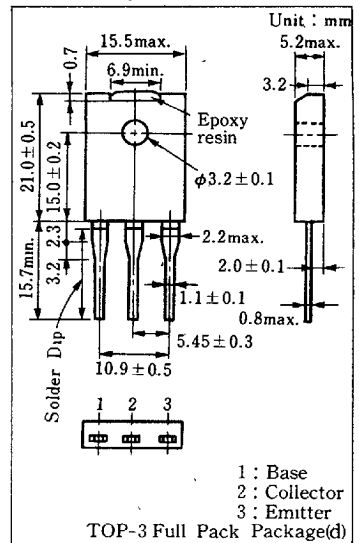
■ Absolute Maximum Ratings (T_c=25°C)

Item	Symbol	Value	Unit															
Collector-base voltage	V _{CB0}	1500	V															
Collector-emitter voltage	V _{CES}	1500	V															
	V _{CEO}	700	V															
Emitter-base voltage	V _{EBO}	7	V															
Peak collector current	I _{CP}	10	A															
Collector current	I _C	3.5	A															
Base current	I _B	1.5	A </tr <tr> <td rowspan="2">Collector power dissipation</td> <td rowspan="2">P_C</td> <td>T_C=25°C</td> <td>60</td> <td rowspan="2">W</td> </tr> <tr> <td>T_a=25°C</td> <td>3</td> </tr> <tr> <td>Junction temperature</td> <td>T_J</td> <td>150</td> <td>°C</td> </tr> <tr> <td>Storage temperature</td> <td>T_{stg}</td> <td>-55 ~ +150</td> <td>°C</td> </tr>	Collector power dissipation	P _C	T _C =25°C	60	W	T _a =25°C	3	Junction temperature	T _J	150	°C	Storage temperature	T _{stg}	-55 ~ +150	°C
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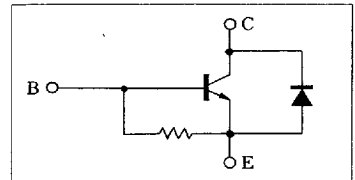
■ Electrical Characteristics (T_c=25°C)

Item	Symbol	Condition	min.	typ.	max.	Unit
Collector cutoff current	I _{CBO}	V _{CB} =750V, I _E =0			10	μA
		V _{CB} =1500V, I _E =0			1	mA
Emitter-base voltage	V _{EBO}	I _E =500mA, I _C =0	7			V
DC current gain	h _{FE}	V _{CE} =5V, I _C =0.5A	5		25	
		V _{CE} =10V, I _C =3A	4			
Collector-emitter saturation voltage	V _{CE(sat)}	I _C =3A, I _B =0.8A			8	V
Base-emitter saturation voltage	V _{BE(sat)}	I _C =3A, I _B =0.8A			1.5	V
Transition frequency	f _T	V _{CE} =10V, I _C =0.5A, f=0.5MHz		2		MHz
Storage time (L load)	t _{stg}	I _C =3A, I _{B1} =0.8A			8	μs
Collector current fall time (L load)	t _f	I _{B2} =-0.8A, L _{leak} =5μH			0.8	μs
Storage time (R load)	t _{stg}	I _C =3A, I _{B1} =0.8A		1.5		μs
Collector current fall time (R load)	t _f	I _{B2} =-1.6A, V _{CC} =200V		0.2		μs
Diode forward voltage	V _f	I _C =-3.5A, I _B =0			2	V

■ Package Dimensions



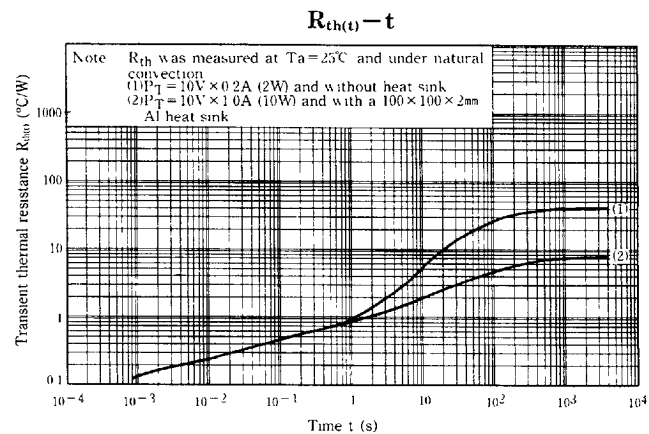
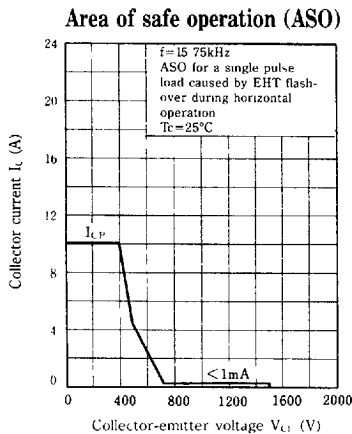
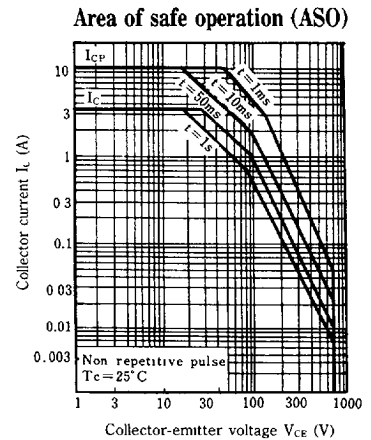
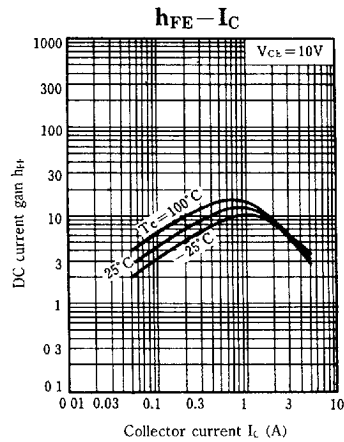
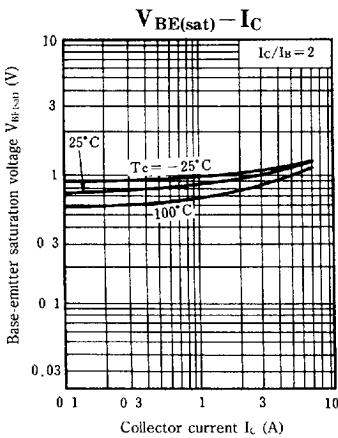
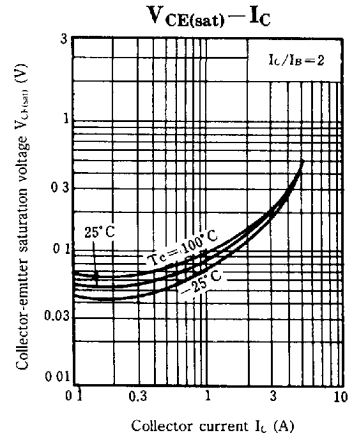
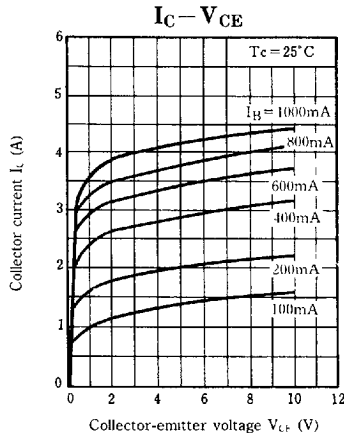
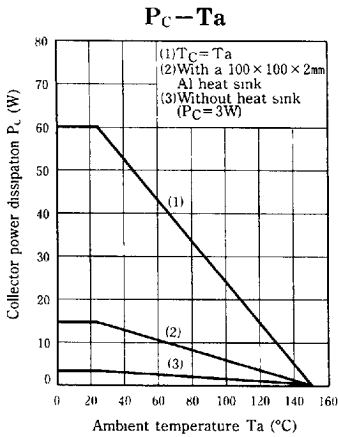
■ Inner Circuit



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Panasonic

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